

92 45.(Amended) A method of operating a memory device having a plurality of memory cells, comprising:

generating a first read voltage;

applying said first read voltage to a terminal of a first cell of the plurality of memory cells;

generating a first read result in response to said applying said first read voltage;

generating a second read voltage;

applying said second read voltage to said terminal of said first cell;

generating a second read result in response to said applying said ~~first~~ second read voltage; and

determining from said first and second read results whether data storage of the memory device is deteriorated.

46.(Amended) The method of claim 45, further comprising:

rewriting the data content stored in ~~to~~ said plurality of memory cells in response to determining from said first and second read results that the data storage of the memory device is deteriorated.

47.(Amended) The method of claim 46, wherein the data content rewritten ~~values written~~ into said plurality of memory cells in said rewriting are determined based on error correction code (ECC).